

**Second mid-term test of Condensed Matter Physics - January 17th 2023**  
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**Exercise 1: Tight binding.**

Consider a one-dimensional lattice with lattice spacing  $a = 0.6$  nm. The lattice hosts a biatomic compound AB, and the A–B bonds in the crystal are alternately short and long, with length  $a_S = a/3 = 0.2$  nm and  $a_L = 2a/3 = 0.4$  nm, respectively (see Fig. 1; NOTICE that the final solution does not depend on the specific values of  $a_S$  and  $a_L$ , as long as  $a_S + a_L = a$ ). The outer orbitals of both A and B atoms are  $s$  orbitals, with atomic energies  $\varepsilon_A = -5.0$  eV and  $\varepsilon_B = -5.3$  eV, respectively. Assume that the electron states of the given lattice can be described within the tight-binding approach with attractive lattice potential, and that the transfer integral for short and long bonds are  $\gamma_S = 0.3$  eV and  $\gamma_L = 0.1$  eV, respectively. All other transfer integrals, all overlap integrals and the  $\beta$  integrals can be neglected altogether. Indicate with  $k \in [-\frac{\pi}{a}, \frac{\pi}{a}]$  the one-dimensional wave vector, and with  $b_A$  and  $b_B$  the coefficients of the linear combination of  $s$  orbitals of A and B atoms.

1. [5 points] Find the expressions of the dispersion laws for the conduction and valence band, respectively,  $\varepsilon_c(k)$  and  $\varepsilon_v(k)$ .
2. [4 points] Calculate the numerical value of the velocity  $v_k$  of an electron in the valence band with with wave vector  $k = \frac{\pi}{2a}$ .
3. [6 points] Determine the numerical value of the band gap  $E_g$  that separates the conduction and valence band and its location within the first Brillouin zone.

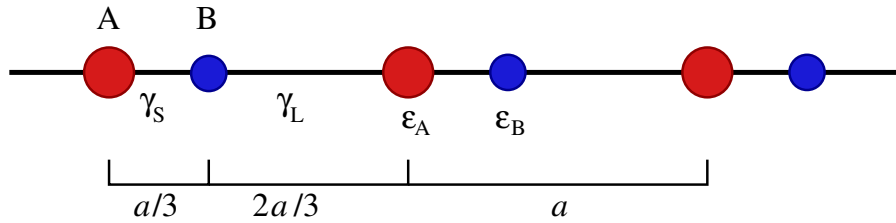


Fig. 1.

**Exercise 2: Semiconductors.**

Consider an intrinsic three-dimensional semiconductor, whose chemical potential  $\mu_i$  stays in the middle of the gap independently of the temperature. At  $T = 500$  K the density of electrons in the conduction band is  $n_c = 1.27 \times 10^{14} \text{ cm}^{-3}$ , while at  $T = 600$  K  $n_c = 9.92 \times 10^{14} \text{ cm}^{-3}$ .

1. [6 points] Determine the numerical value of the band gap energy  $E_g$ .
2. [5 points] Determine the numerical value of the electron and hole effective masses,  $m_c$  and  $m_v$ , respectively.
3. [4 points] It is found that the conductivity of the semiconductor at  $T = 500$  K is  $\sigma = 20 \Omega^{-1} \cdot \text{m}^{-1}$  and that the electron mobility  $\tilde{\mu}_e$  is four times greater than the hole mobility  $\tilde{\mu}_h$ . Determine the electron and hole relaxation time (namely, the average time between two collisions),  $\tau_e$  and  $\tau_h$ , respectively.

[Useful constants and conversion factors: the reduced Planck constant is  $\hbar = 1.05 \times 10^{-34}$  J·s, the Boltzmann constant is  $\kappa_B = 1.38 \times 10^{-23}$  J·K<sup>-1</sup>, the elementary charge is  $e = 1.60 \times 10^{-19}$  C, the free electron mass is  $m_0 = 9.11 \times 10^{-31}$  kg; 1 eV corresponds to a temperature of  $1.16 \times 10^4$  K or to an energy of  $1.60 \times 10^{-19}$  J].

**Solution**  
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**Exercise 1.**

1. We introduce the complex quantity

$$\Gamma_k \equiv \gamma_S e^{ika_S} + \gamma_L e^{-ika_L}.$$

Then, the tight-binding equations take the form of the  $2 \times 2$  system of homogeneous equations

$$\begin{cases} [\varepsilon_A - \varepsilon(k)]b_A - \Gamma_k b_B = 0, \\ -\Gamma_k^* b_A + [\varepsilon_B - \varepsilon(k)]b_B = 0. \end{cases}$$

The systems admits non-trivial solutions if the energy  $\varepsilon(k)$  is an eigenvalue of the linear problem,

$$\varepsilon_{\pm}(k) = \frac{\varepsilon_A + \varepsilon_B}{2} \pm \sqrt{\left(\frac{\varepsilon_A - \varepsilon_B}{2}\right)^2 + |\Gamma_k|^2},$$

with

$$|\Gamma_k|^2 = \gamma_S^2 + \gamma_L^2 + 2\gamma_S\gamma_L \cos(ka),$$

where we used the fact that  $a_S + a_L = a$ . The conduction band is  $\varepsilon_c(k) = \varepsilon_+(k)$  and the valence band is  $\varepsilon_v(k) = \varepsilon_-(k)$ .

2. The required velocity is

$$v_{k=\frac{\pi}{2a}} = \frac{1}{\hbar} \frac{\partial \varepsilon_v}{\partial k} \Big|_{k=\frac{\pi}{2a}} = \frac{a\gamma_S\gamma_L \sin(ka)}{\hbar \sqrt{\left(\frac{\varepsilon_A - \varepsilon_B}{2}\right)^2 + |\Gamma_k|^2}} \Big|_{k=\frac{\pi}{2a}} = \frac{a\gamma_S\gamma_L}{\hbar \sqrt{\left(\frac{\varepsilon_A - \varepsilon_B}{2}\right)^2 + \gamma_S^2 + \gamma_L^2}} = 7.81 \times 10^4 \text{ m/s}.$$

3.  $|\Gamma_k|^2$  is minimum at  $k = \frac{\pi}{a}$ , where  $|\Gamma_k|^2 = (\gamma_S - \gamma_L)^2$  and is maximum at  $k = 0$ , where  $|\Gamma_k|^2 = (\gamma_S + \gamma_L)^2$ . Then, the band gap is located at  $k = \frac{\pi}{a}$  and

$$E_g = 2\sqrt{\left(\frac{\varepsilon_A - \varepsilon_B}{2}\right)^2 + (\gamma_S - \gamma_L)^2} = 0.5 \text{ eV}.$$

**Exercise 2.**

1. The fact that the chemical potential  $\mu_i$  is independent of the temperature indicates that  $m_c = m_v$ . Furthermore, since  $\tilde{\mu}_e = 4\tilde{\mu}_h$  and the electron and hole masses are equal, we deduce that  $\tau_e = 4\tau_h$ . The ratio of the densities of electrons in the conduction band at the two given temperatures is

$$\frac{n_c(T = 500 \text{ K})}{n_c(T = 600 \text{ K})} = \left(\frac{5}{6}\right)^{3/2} e^{\frac{E_g}{2\kappa_B} \left(\frac{1}{600 \text{ K}} - \frac{1}{500 \text{ K}}\right)}.$$

The text assigns to this ratio the value 0.128, hence  $E_g = 0.921 \text{ eV}$ .

2. From

$$n_c(T = 500 \text{ K}) = 2.5 \left(\frac{5 m_c}{3 m_0}\right)^{3/2} e^{-\frac{0.921 \text{ eV}}{2\kappa_B 500 \text{ K}}} 10^{19} \text{ cm}^{-3},$$

one finds  $m_c = 0.220 m_0$ .

3. We know that  $\sigma = en_i(\tilde{\mu}_e + \tilde{\mu}_h) = 5en_i\tilde{\mu}_h = 5e^2 n_c \tau_h / m_c$ . Then, one finds  $\tau_h = 2.46 \times 10^{-13} \text{ s}$  and  $\tau_e = 4\tau_h = 9.84 \times 10^{-13} \text{ s}$ .